

Table 1. Symbol

VDRM

BTA206X-800ET

3Q Hi-Com Triac Rev. 2 — 20 December 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used where "high junction operating temperature" capability ($T_i = 150$ °C) is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls for home appliancesRefrigeration and air-conditioner

compressor controls

	reference data		
Quick reference data			
Parameter	Conditions	Min	Тур
repetitive peak off-sta voltage	ate	-	-

full sine wave; $T_{i(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; 60 А **I**TSM non-repetitive peak on-state -_ see Figure 4; see Figure 5 current °C 150 Τi junction temperature -full sine wave; $T_h \le 114$ °C; see Figure 1; 6 А RMS on-state current _ I_{T(RMS)} see Figure 2; see Figure 3



Unit

V

Max 800

3Q Hi-Com Triac

		linueu				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 7</u>	-	-	10	mA
		$V_D = 12 V; I_T = 0.1 A; T2+G-; T_j = 25 °C;$ see Figure 7	-	-	10	mA
		$V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C;$ see <u>Figure 7</u>	-	-	10	mA
Dynamic of	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	50	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 150 °C; I _{T(RMS)} = 6 A; dV _{com} /dt = 1 V/µs; gate open circuit	5	-	-	A/ms

Table 1. Quick reference data ...continued

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2	mb	T2-T1
3	G	gate		Sym051
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

2 3

3. Ordering information

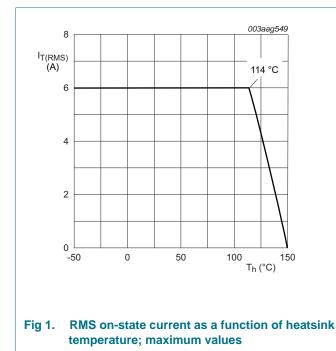
Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BTA206X-800ET	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

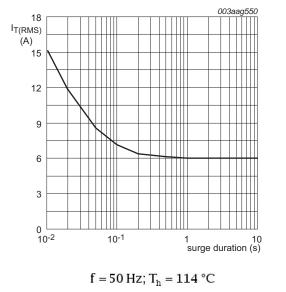
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 114 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	6	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	60	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	66	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	18	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 10 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Т _і	junction temperature		-	150	°C

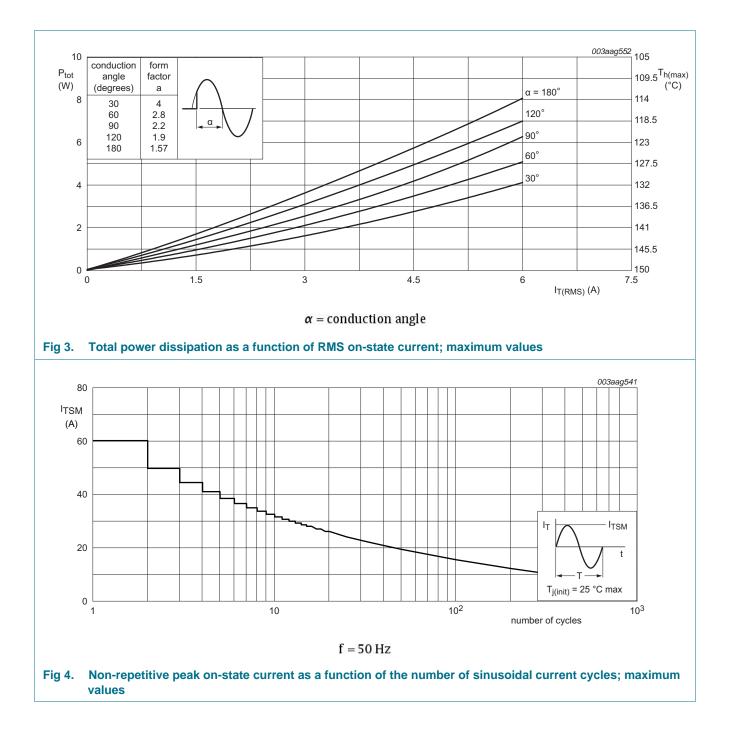






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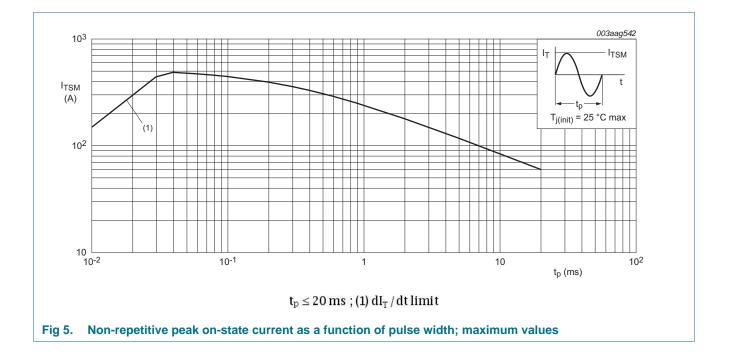
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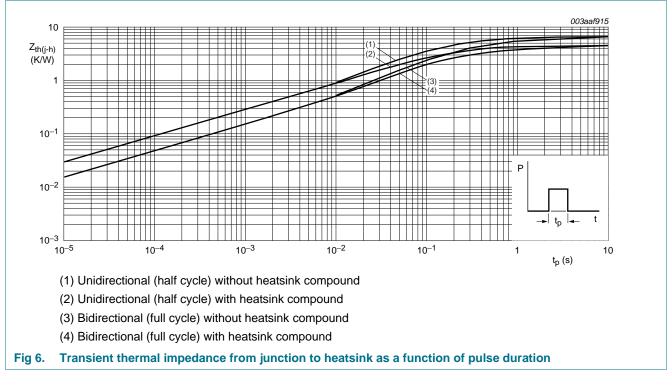
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see <u>Figure 6</u>	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

Table 6.	Isolation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; f = 1 MHz; $T_h = 25 \text{ °C}$	-	10	-	pF

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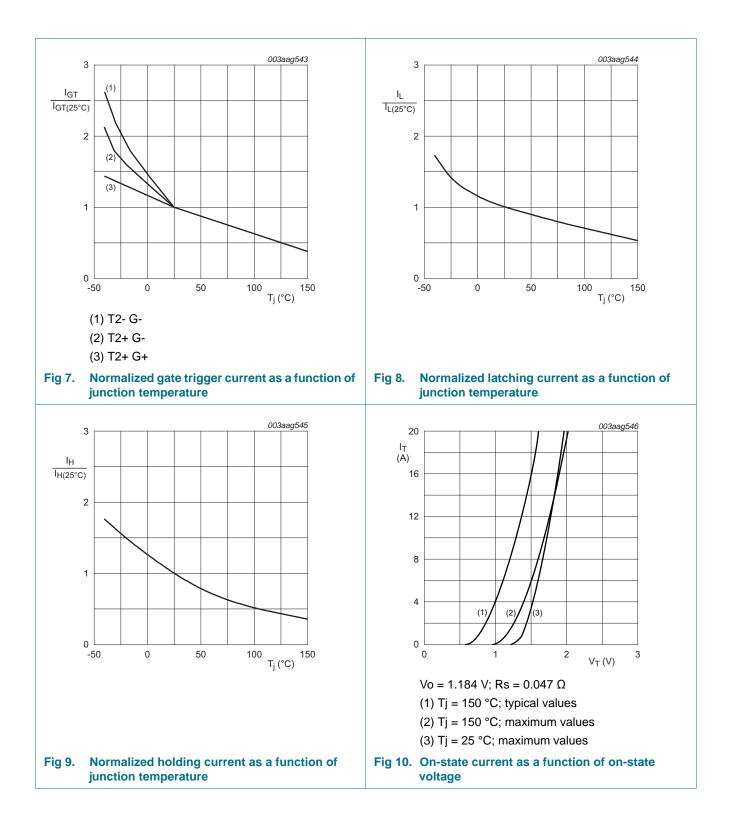
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G+}; \text{T}_j = 25 \text{ °C};$ see <u>Figure 7</u>	-	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see Figure 7	-	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2+ G+}; \text{T}_j = 25 \text{ °C};$ see Figure 8	-	-	25	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	25	mA
I _H	holding current	$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{100000000000000000000000000000000000$	-	-	15	mA
V _T	on-state voltage	I _T = 7 A; see <u>Figure 10</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; see <u>Figure 11</u>	-	0.8	1.5	V
		$V_D = 400 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 150 ^\circ\text{C}$	0.25	-	-	V
I _D	off-state current	V _D = 800 V; T _j = 150 °C	-	0.4	2	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	50	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{T}_j = 150 \text{ °C}; \text{I}_{\text{T}(\text{RMS})} = 6 \text{ A}; $ $dV_{\text{com}}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	1	-	-	A/m
		$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 10 \text{ V}/\mu s;$ gate open circuit	2	-	-	A/m
		$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 1 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	5	-	-	A/m

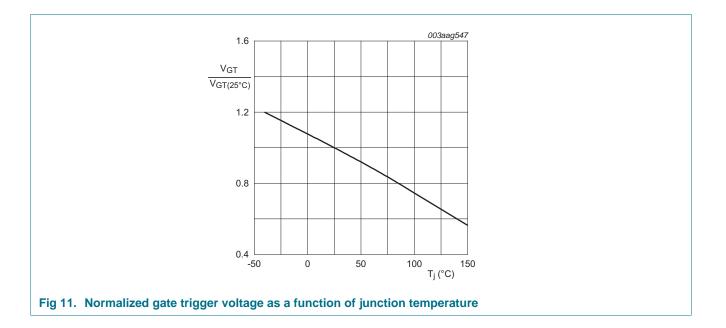
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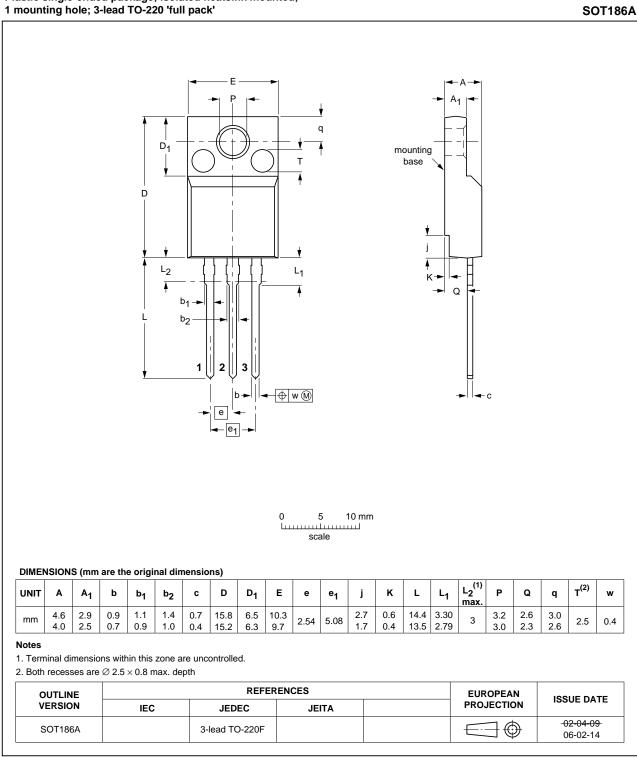


BTA206X-800ET Product data sheet

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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

Fig 12. Package outline SOT186A (TO-220F)

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9. Revision history

Table 8.Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA206X-800ET v.2	20111220	Product data sheet	-	BTA206X-800ET v.1
Modifications:	 Various changes t 	o content.		
BTA206X-800ET v.1	20110822	Product data sheet	-	-

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10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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